| Form PTO 1449 | Atty. Docket Number | Serial Number |
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| U.S. Department of Commerce<br>Patent and Trademark Office | HITA.0501 | To be assigned |
| | Applicant<br>SAITO et al | |
| Information Disclosure Statement by Applicant | Filing Date<br>Concurrently herewith | Group |

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| Examiner Initial | | Document Number | Date | Name | Class | Subclass | Filing Date |
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